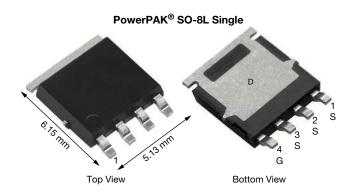


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Vishay Siliconix

# Automotive N-Channel 80 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V <sub>DS</sub> (V)	80			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0125			
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.0160			
I <sub>D</sub> (A)	46			
Configuration	Single			

#### **FEATURES**

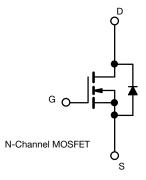
- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rg and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





HALOGEN

FREE



ORDERING INFORMATION	
Package	PowerPAK SO-8L
Lead (Pb)-free and halogen-free	SQJA84EP-T1 (for detailed order number please see <a href="https://www.vishay.com/doc?79771">www.vishay.com/doc?79771</a> )

ABSOLUTE MAXIMUM RATING	<b>S</b> (T <sub>C</sub> = 25 °C, unles	s otherwise noted	1)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	80	V	
Gate-source voltage		$V_{GS}$	V <sub>GS</sub> ± 20		
Continuous drain current	T <sub>C</sub> = 25 °C	1	46		
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	26.5		
Continuous source current (diode conduction)		I <sub>S</sub>	50	Α	
Pulsed drain current <sup>a</sup>		I <sub>DM</sub>	100		
Single pulse avalanche current		I <sub>AS</sub>	27		
Single pulse avalanche energy	Ingle pulse avalanche energy		36	mJ	
Maximum power dissipation 8	T <sub>C</sub> = 25 °C	Б	55	W	
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 125 °C	$P_{D}$	18	VV	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C	
Soldering recommendations (peak temperature) c, d		-	260		

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount b	R <sub>thJA</sub>	70	°C/W
Junction-to-case (drain)		R <sub>thJC</sub>	2.7	G/VV

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)

S22-0167-Rev. B, 14-Feb-2022

- c. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- d. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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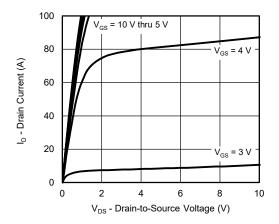
PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static				'	•		
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		80	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	= V <sub>GS</sub> , I <sub>D</sub> = 250 μA	1.5	2.0	2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$0 \text{ V}, \text{ V}_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 80 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 80 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 80 V, T <sub>J</sub> = 175 °C	-	-	150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A	-	0.0102	0.0125	
Drain aguras an atata registance 3	В	V <sub>GS</sub> = 4.5 V	I <sub>D</sub> = 8 A	-	0.0131	0.0160	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 125 °C	-	-	0.0207	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 10 A, T <sub>J</sub> = 175 °C	-	-	0.0258	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		-	50	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>			-	1565	2100	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	785	1100	pF
Reverse transfer capacitance	C <sub>rss</sub>	7		-	35	50	
Total gate charge <sup>c</sup>	Qg			-	21	35	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V	$V_{DS} = 40 \text{ V}, I_{D} = 5 \text{ A}$	-	4	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>	7		-	3	-	
Gate resistance	Rg		f = 1 MHz	0.18	0.40	0.62	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	11	18	
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{\mathrm{DD}}$	= 40 V, $R_L$ = 8 $\Omega$	-	5	10	1
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 5 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	23	35	ns
Fall time <sup>c</sup>	t <sub>f</sub>	7		-	7	15	
Source-Drain Diode Ratings and Char	racteristics <sup>b</sup>	•			•		
Pulsed current <sup>a</sup>	I <sub>SM</sub>			-	-	100	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> :	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0		0.82	1.2	V
	•			1			

#### Notes

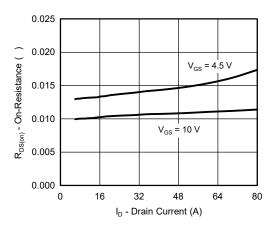
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

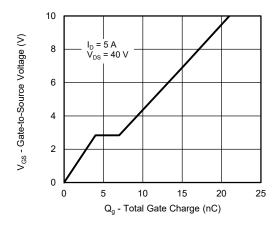




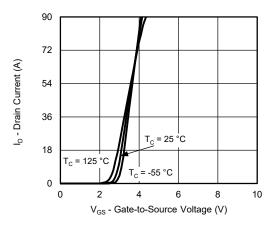
#### **Output Characteristics**



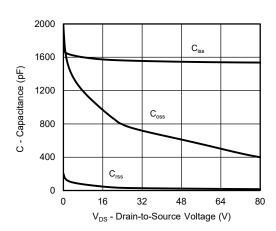
On-Resistance vs. Drain Current



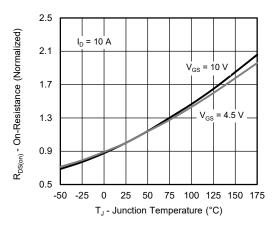
**Gate Charge** 



**Transfer Characteristics** 



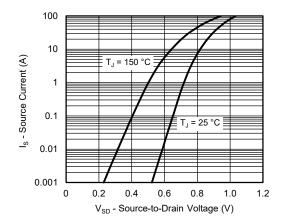
Capacitance



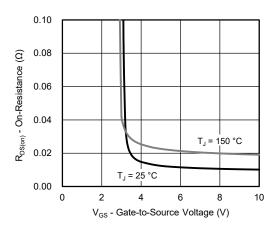
On-Resistance vs. Junction Temperature

For technical questions, contact: automoste

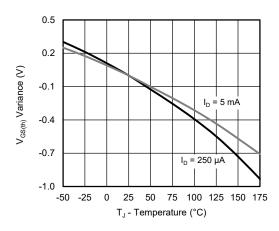




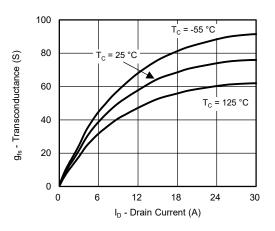
**Source Drain Diode Forward Voltage** 



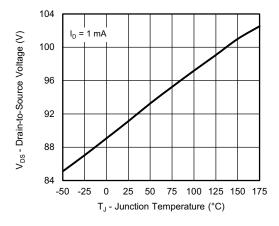
On-Resistance vs. Gate-to Source Voltage



**Threshold Voltage** 



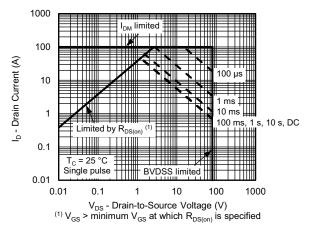
Transconductance



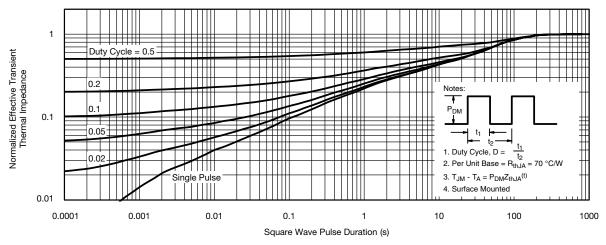
**Drain Source Breakdown vs. Junction Temperature** 

For technical questions, contact: automoste



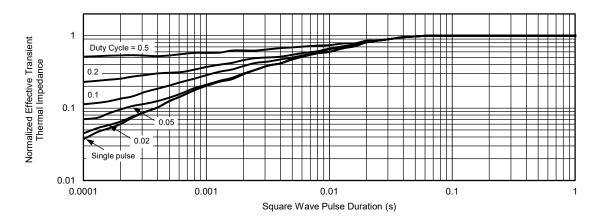


Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient





Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

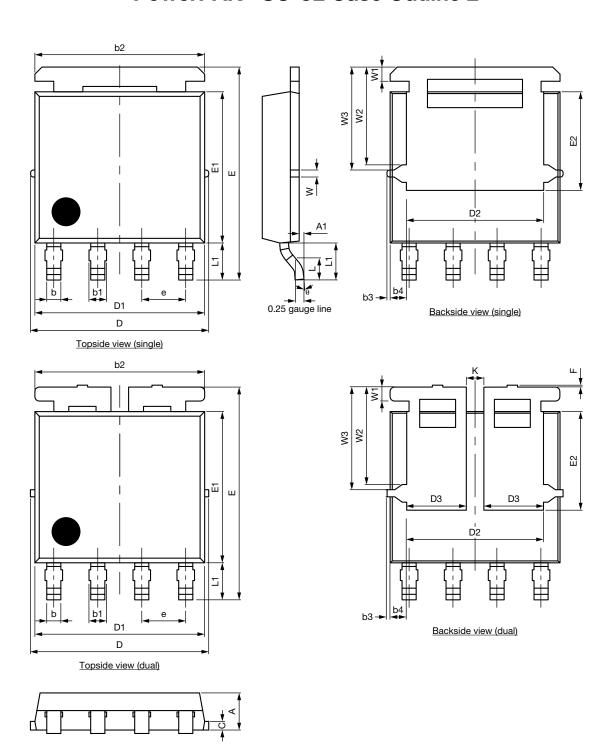
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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# PowerPAK® SO-8L Case Outline 2



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DIM		MILLIMETERS			INCHES		
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094	_		0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC	•	0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51	•	0.020			
W		0.23		0.009			
W1	0.41		0.016				
W2		2.82		0.111			
W3		2.96		0.117			
θ	0°	-	10°	0°	-	10°	

ECN: C21-1498-Rev. C, 01-Nov-2021

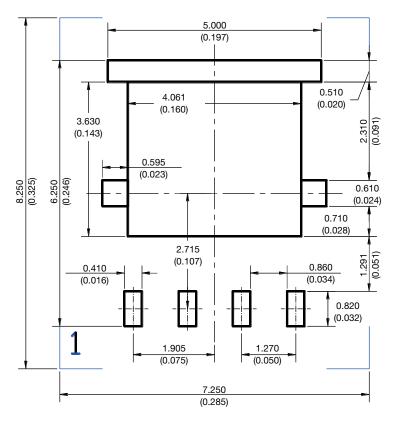
DWG: 6044

#### Note

• Millimeters will govern



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



## **Legal Disclaimer Notice**

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